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<u>Fairchild Semiconductor</u> 2N5772

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2N5772

NPN Switching Transistor

• Sourced from process 22.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings * T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	15	V
V _{CBO}	Collector-Base Voltage	40	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continued	300	mA
T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.

 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charact	eristics		•		•
BV _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	15		V
BV _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, V_{BE} = 0$	40		V
BV _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	40		V
BV _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20V, I_{E} = 0$		0.5	μΑ
I _{CES}	Collector Cutoff Current	$V_{CE} = 20V, V_{BE} = 0$		0.5	μΑ
	Fasition Contact Comment	$V_{CE} = 20V, V_{BE} = 0, T_a = 65^{\circ}C$		3.0	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0V, I_{C} = 0$		100	μΑ
On Charact	eristics *				
h _{FE}	DC Current Gain	$V_{CE} = 0.4V, I_{C} = 30mA$	30	120	
		$V_{CE} = 0.5V, I_{C} = 100mA$	25		
		$V_{CE} = 1.0V, I_{C} = 300mA$	15		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 30 \text{mA}, I_B = 3.0 \text{mA}$		0.2	V
		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		0.28	V
		$I_C = 300 \text{mA}, I_B = 3.0 \text{mA}$		0.5	V
V _{BF} (sat)	Base-Emitter Saturation Voltage	I _C = 30mA, I _B = 3.0mA	0.73	0.95	V
52.		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		1.2	V
		$I_C = 300 \text{mA}, I_B = 3.0 \text{mA}$		1.7	V
Small Signa	I Characteristics		•		
C _{cb}	Collector-Base Capacitance	$V_{CB} = 5.0V, I_{E} = 0, f = 1MHz$		5.0	pF
C _{eb}	Emitter-Base Capacitance	$V_{CB} = 5.0V, I_{C} = 0, f = 1MHz$		8.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 300 \text{mA}, V_{CE} = 10 \text{V}, f = 100 \text{MHz}$	3.5		
	e Width ≤ 300µs, Duty Cycle ≤ 2.0%	1			

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Electrical Characteristics Ta=25°C unless otherwise noted (Continued)

Symbol	Parameter	Test Condition	Min.	Max.	Units	
Switching C	Switching Characteristics					
t _s	Storage Time	I _C = 300mA, V _{CC} = 10V		20	ns	
t _{on}	Turn-On Time	$I_{B1} = I_{B2} = 30 \text{mA}$		18	ns	
t _{off}	Turn-Off Time			28	ns	

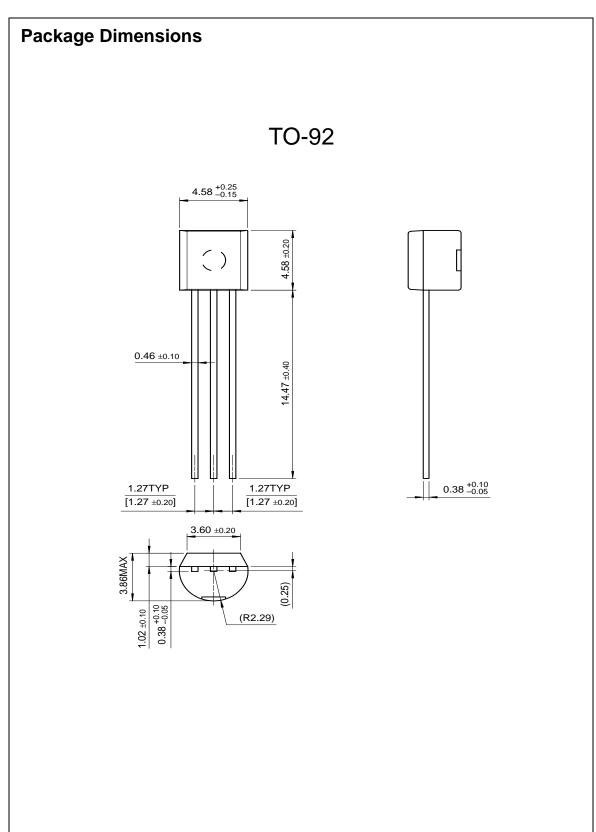
Thermal Characteristics $T_a=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

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Dimensions in Millimeters

Distributor of Fairchild Semiconductor: Excellent Integrated System Limited

Datasheet of 2N5772 - TRANS NPN 15V 0.3A TO-92

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